

# NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE60H30T uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

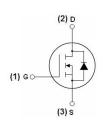
#### **General Features**

- $V_{DS}$  =60V, $I_{D}$  =300A  $R_{DS(ON)}$  <3.1m $\Omega$  @  $V_{GS}$ =10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% ΔVds TESTED!



Schematic diagram



TO-247 top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60H30T	NCE60H30T	TO-247	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	300	Α
Drain Current-Continuous(Tc=100°ℂ)	I <sub>D</sub> (100°C)	210	Α
Pulsed Drain Current	I <sub>DM</sub>	900	Α
Maximum Power Dissipation <sup>(Note 1)</sup>	P <sub>D</sub>	400	W
Derating factor		2.67	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	3125	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	$^{\circ}$

#### **Thermal Characteristic**



# http://www.ncepower.com

# NCE60H30T

İ	Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	0.38	°C/W
	Thermal Resistance, Junction-to-Case (1982)	<b>K</b> θJC	0.38	C/VV

# Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.3	1.7	2.1	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	1.8	2.1	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =20V,I <sub>D</sub> =40A	-	120	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,	-	17993	-	PF
Output Capacitance	Coss		-	1255	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	992	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	50	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $R_L$ =0.6 $\Omega$	-	90	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}\text{=}10V, R_{G}\text{=}2.5\Omega$	-	280	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	75	-	nS
Total Gate Charge	Qg	V 20VI 40A	-	360		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =30V,I <sub>D</sub> =40A,	-	61		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	70		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =40A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	300	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 40A	-	70		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	200		nC
Forward Turn-On Time	ton	Intrinsic turn-on time is neg	ligible (tur	n-on is do	minated b	y LS+LD)

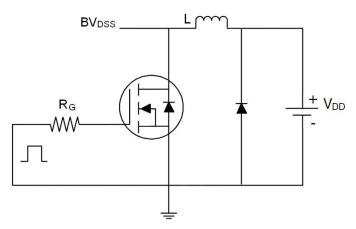
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25  $^{\circ}\text{C}$  ,VDD=30V,VG=10V,L=0.5mH,Rg=25 $\Omega$

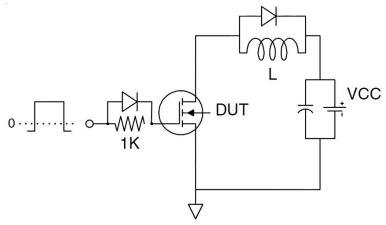


### **Test circuit**

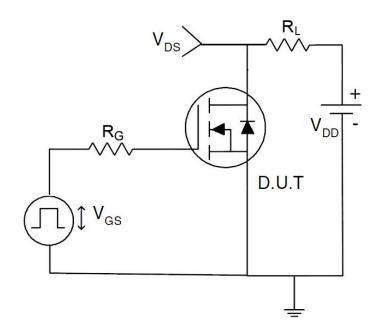
# 1) E<sub>AS</sub> test Circuits



# 2) Gate charge test Circuit:



### 3) Switch Time Test Circuit:





## **Typical Electrical and Thermal Characteristics (Curves)**

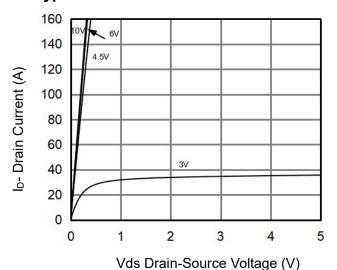
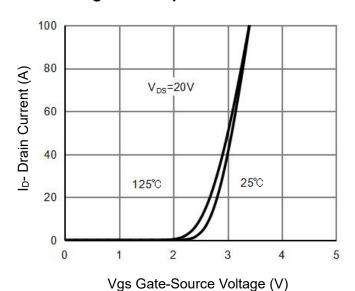


Figure 1 Output Characteristics



**Figure 2 Transfer Characteristics** 

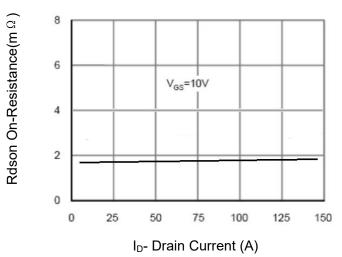


Figure 3 Rdson- Drain Current

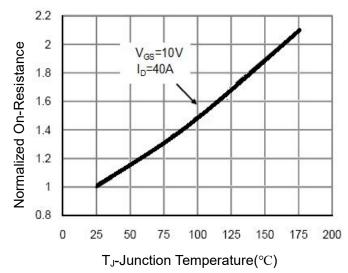
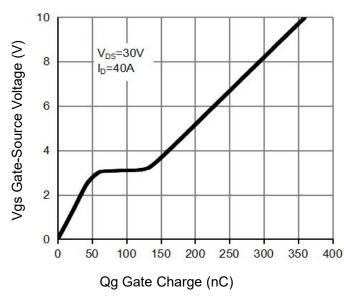


Figure 4 Rdson-JunctionTemperature



**Figure 5 Gate Charge** 

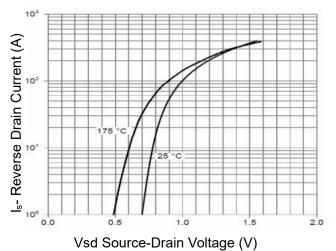


Figure 6 Source- Drain Diode Forward



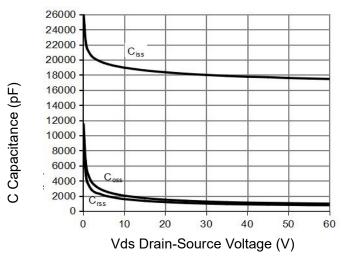


Figure 7 Capacitance vs Vds

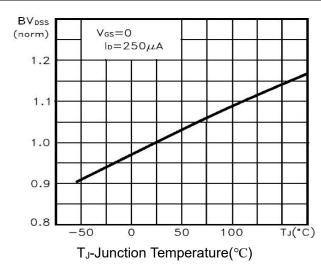
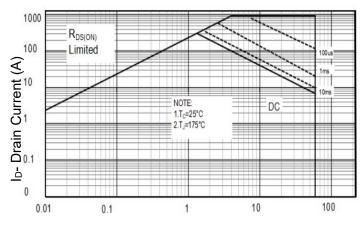
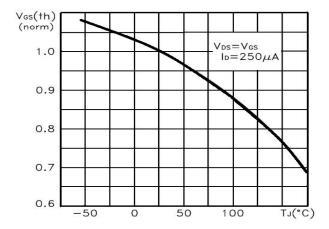


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



T<sub>J</sub>-Junction Temperature(°C)

Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

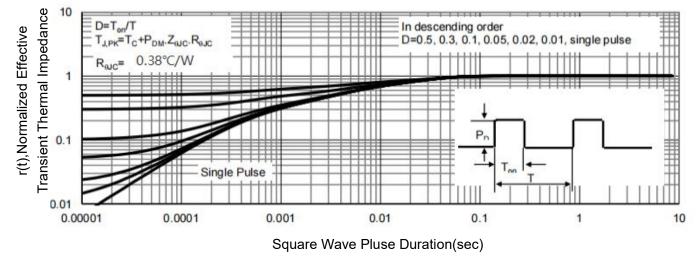
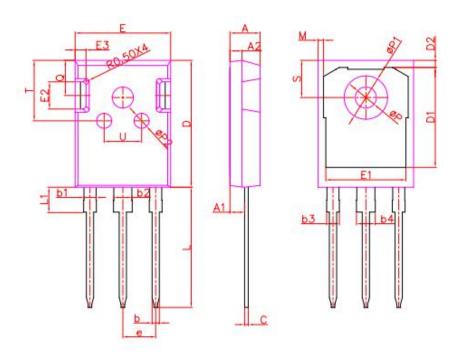


Figure 11 Normalized Maximum Transient Thermal Impedance



# **TO-247 Package Information**



DIM.	MIN.	NOM.	MAX.
Α	4.90	5.00	5.10
A1	2.31	2.432	2.51
A2	1.90	2.00	2.10
b	1.16	1.20	1.26
b1	1.96	2.00	2.06
b2	2.96	3.00	3.06
b3	-	-	2.25
b4	172	-	3.25
С	0.59	0.60	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.26	13.50
E2	4.40	4.50	4.60
E3	1.70	1.80	1.90
е		5.436BSC	
L	19.80	19.90	20.10
L1	_	_	4.30
М	0.35	0.89	0.95
Р	3.40	3.50	3.60
P1	7.00	7.20	7.40
P2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40



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